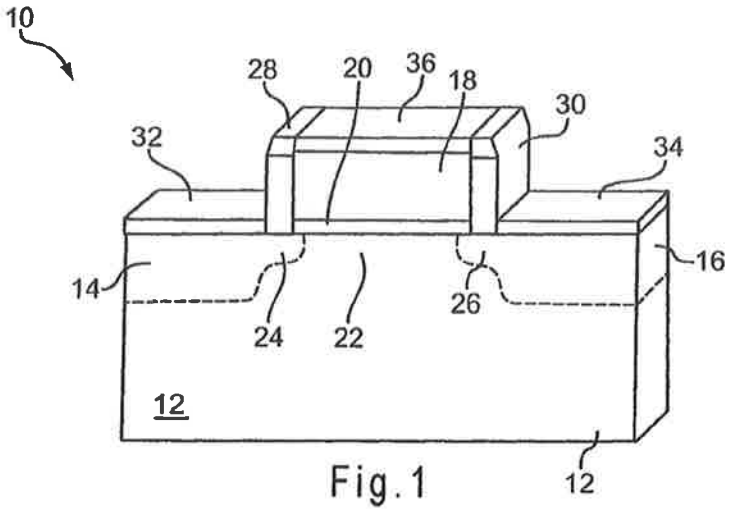

10
28
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36
18
30
32
34
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Fig.1

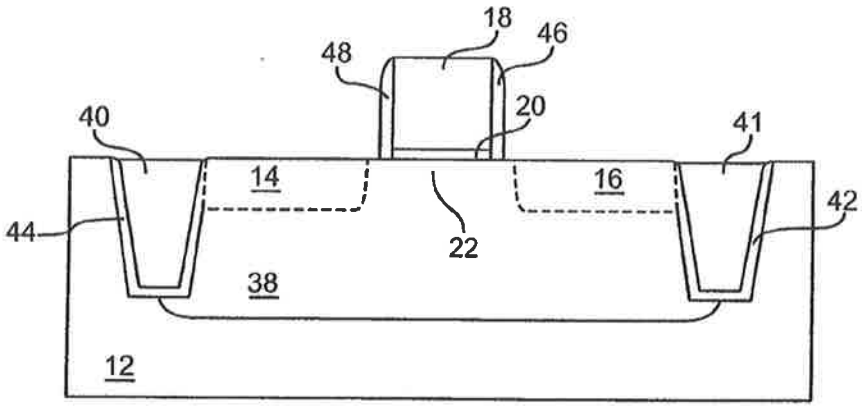

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Fig.2

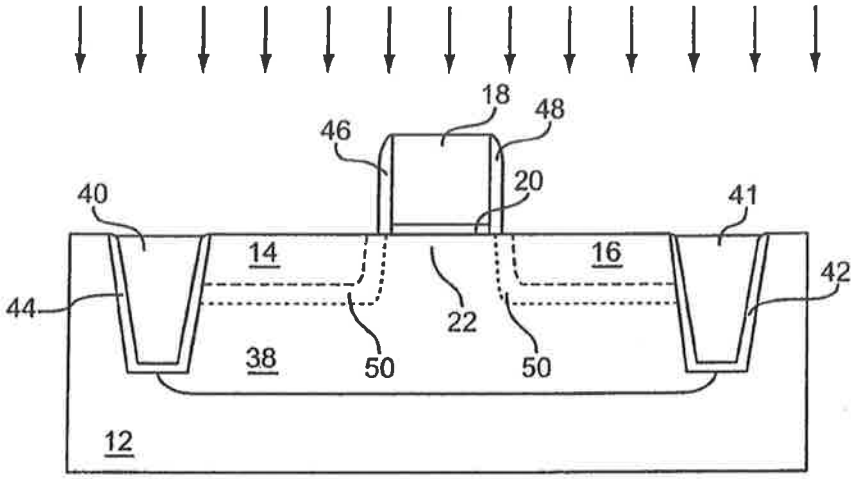

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Fig.3

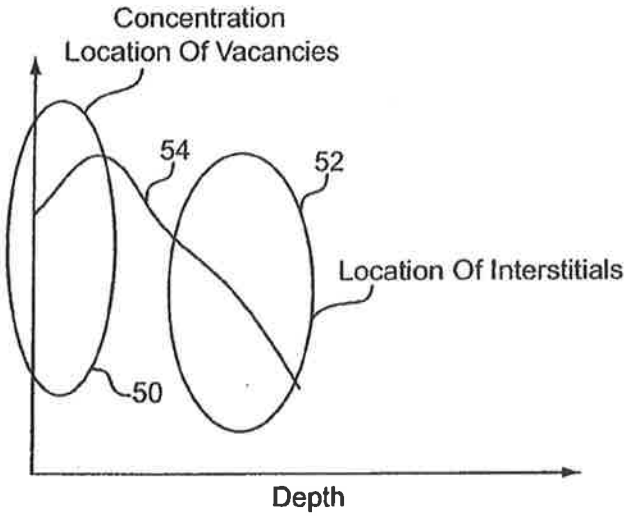

Concentration
Location Of Vacancies
54
52
Location Of Interstitials
50
Depth

Fig.4

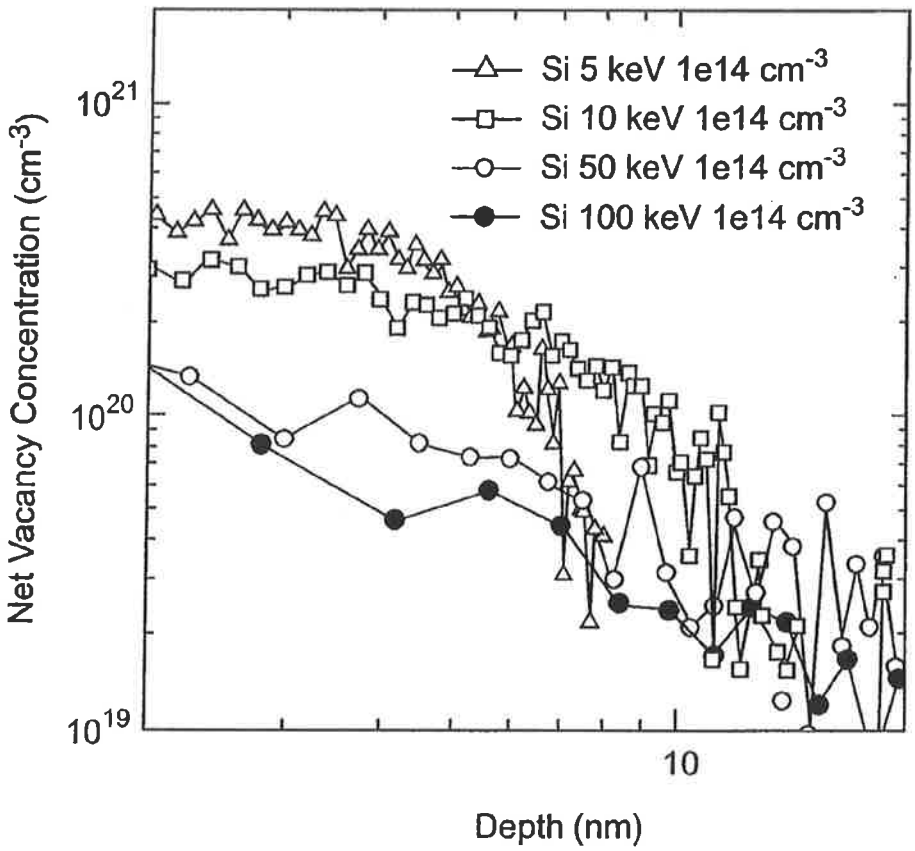

Si 5 keV 1e14 cm-3
Si 10 keV 1e14 cm-3
Si 50 keV 1e14 cm-3
Si 100 keV 1e14 cm-3
Net Vacancy Concentration (cm-3)
10^21
10^20
10^19
10
Depth (nm)

Fig.5

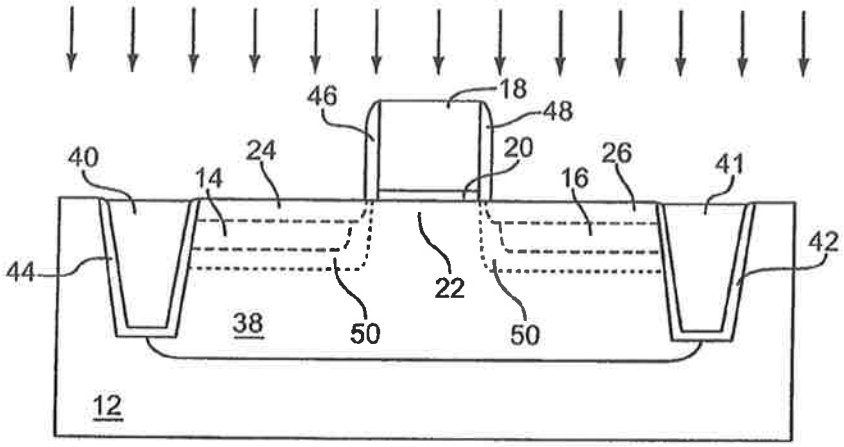

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Fig.6

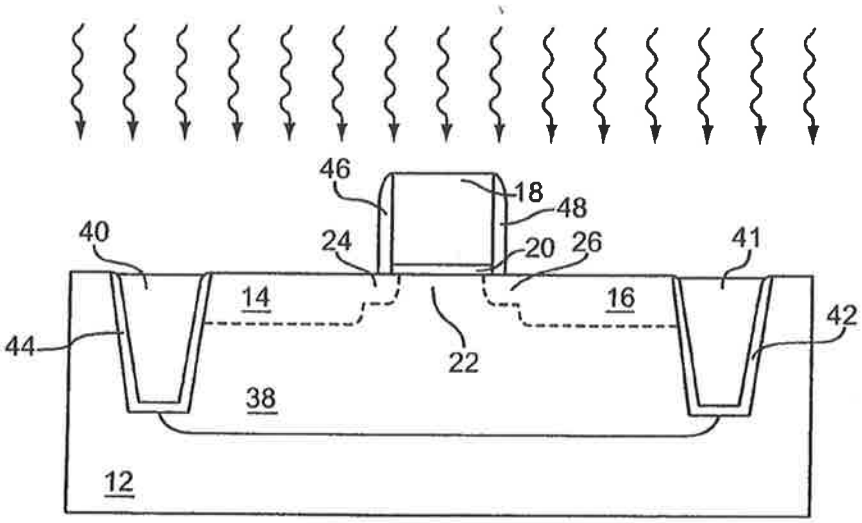

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Fig.7

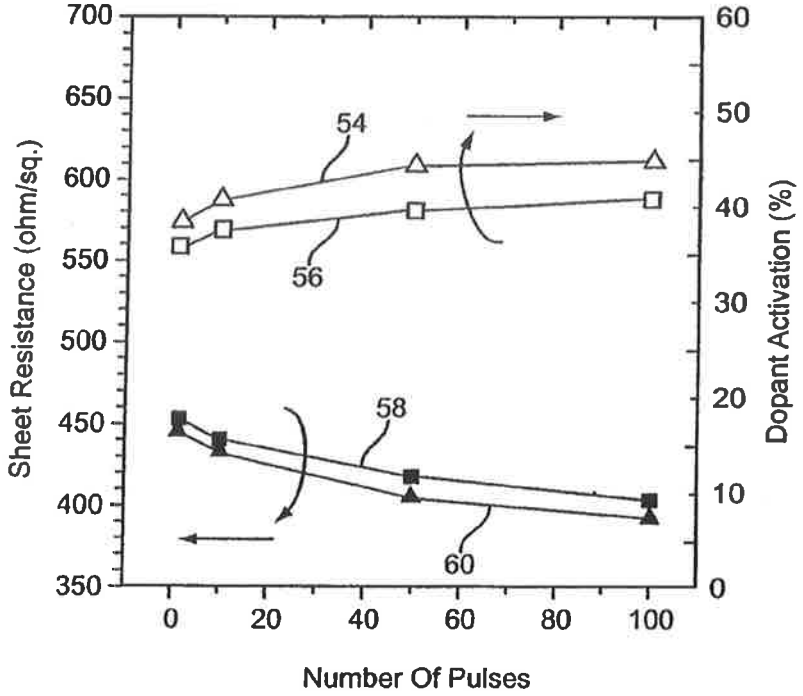

Sheet Resistance (ohm/sq.)
Dopant Activation (%)
Number Of Pulses
700
650
600
550
500
450
400
350
60
50
40
30
20
10
0
0
20
40
60
80
100
54
56
58
60

Fig.8

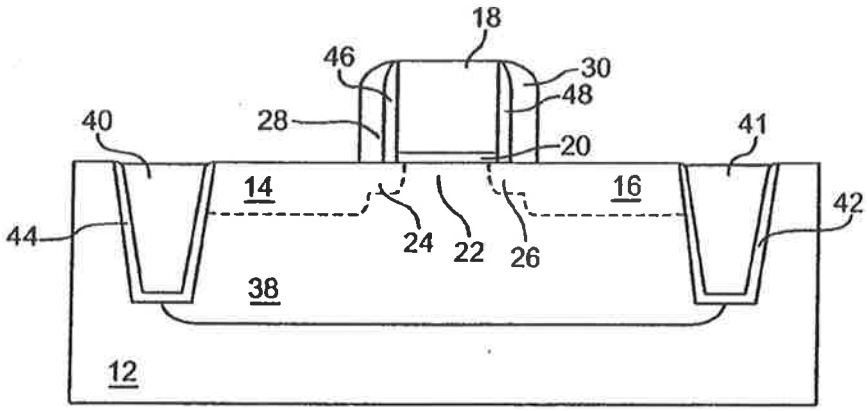

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Fig.9